

Silicon NPN Power Transistors

2SC1116

DESCRIPTION

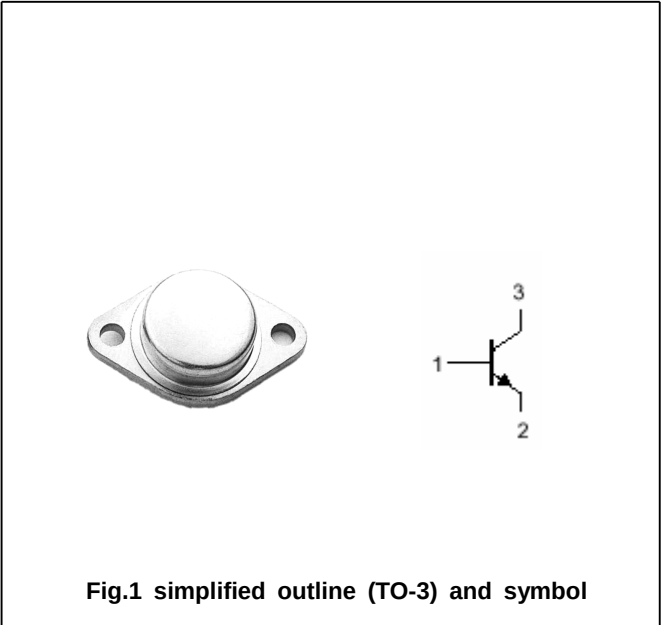
- With TO-3 package
- Wide area of safe operation

APPLICATIONS

- For audio and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		10	A
P_C	Collector power dissipation	$T_C=25^\circ$	100	W
T_j	Junction temperature		150	°
T_{stg}	Storage temperature		-55~150	°

Silicon NPN Power Transistors

2SC1116

CHARACTERISTICS

Tj=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	180			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A ; I_B=0.5A$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=180V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=3A ; V_{CE}=4V$	50			
f_T	Transition frequency	$I_C=1A ; V_{CE}=12V$		10		MHz

Silicon NPN Power Transistors

2SC1116

PACKAGE OUTLINE

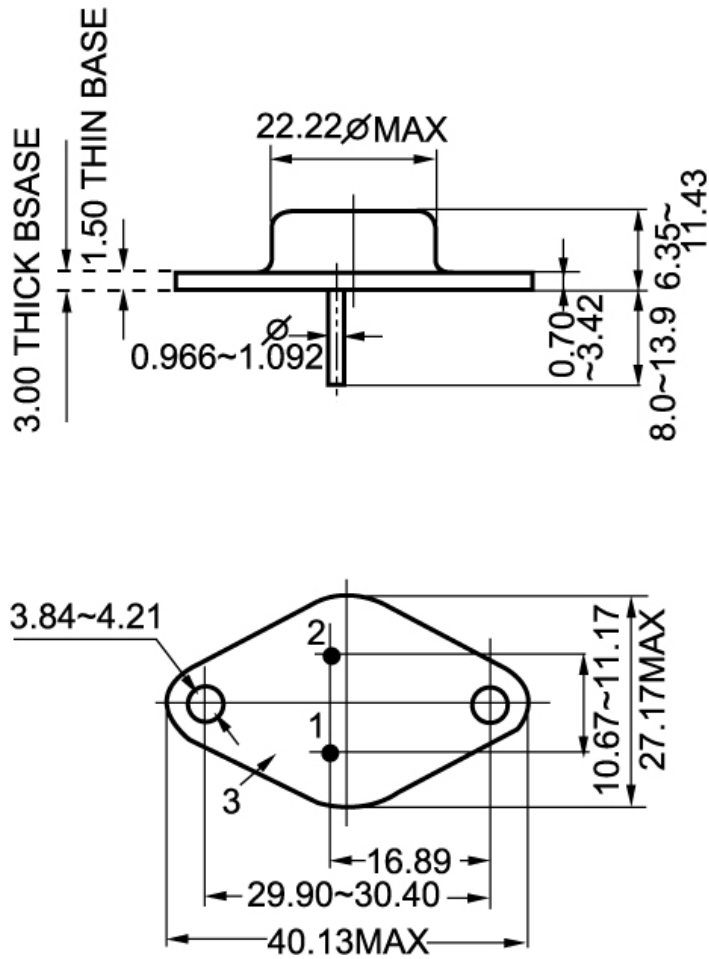


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)